

Parameter	Tr1 and Tr2
$V_{CEO}$	50V
$I_{C(MAX.)}$	100mA
$R_1$	4.7k $\Omega$

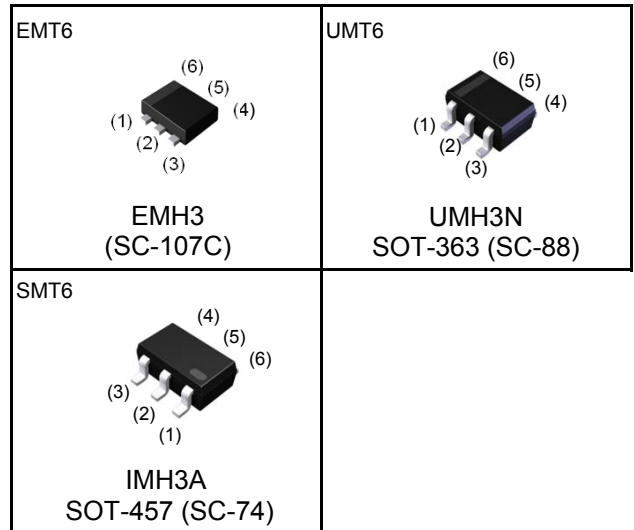
### ●Features

- 1) Built-In Biasing Resistors.
- 2) Two DTC143T chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

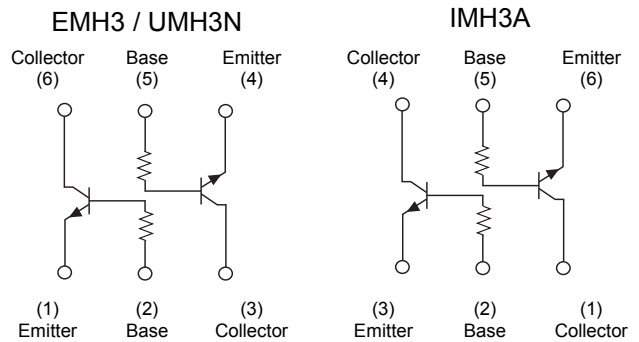
### ●Application

Inverter circuit, Interface circuit, Driver circuit

### ●Outline



### ●Inner circuit



### ●Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMH3	EMT6	1616	T2R	180	8	8,000	H3
UMH3N	UMT6	2021	TN	180	8	3,000	H3
IMH3A	SMT6	2928	T110	180	8	3,000	H3

●Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Values	Unit	
Collector-base voltage	$V_{CBO}$	50	V	
Collector-emitter voltage	$V_{CEO}$	50	V	
Emitter-base voltage	$V_{EBO}$	5	V	
Collector current	$I_{C(MAX.)}^{*1}$	100	mA	
Collector Power dissipation	EMH3 / UMH3N	$P_D^{*2}$	150 (Total) <sup>*3</sup>	mW
	IMH3A		300 (Total) <sup>*4</sup>	mW
Junction temperature	$T_j$	150	°C	
Range of storage temperature	$T_{stg}$	-55 to +150	°C	

●Electrical characteristics (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	$BV_{CBO}$	$I_C = 50\mu A$	50	-	-	V
Collector-emitter breakdown voltage	$BV_{CEO}$	$I_C = 1mA$	50	-	-	V
Emitter-base breakdown voltage	$BV_{EBO}$	$I_E = 50\mu A$	5	-	-	V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 50V$	-	-	0.5	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 4V$	-	-	0.5	$\mu A$
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C / I_B = 5mA / 0.25mA$	-	-	0.15	V
DC current gain	$h_{FE}$	$V_{CE} = 5V, I_C = 1mA,$	100	250	600	-
Input resistance	$R_1$	-	3.5	4.7	5.9	k $\Omega$
Transition frequency	$f_T^{*1}$	$V_{CE} = 10V, I_E = -5mA,$ $f = 100MHz$	-	250	-	MHz

\*1 Characteristics of built-in transistor

\*2 Each terminal mounted on a reference footprint

\*3 120mW per element must not be exceeded.

\*4 200mW per element must not be exceeded.

●Electrical characteristic curves(Ta = 25°C)

Fig.1 Grounded emitter propagation characteristics

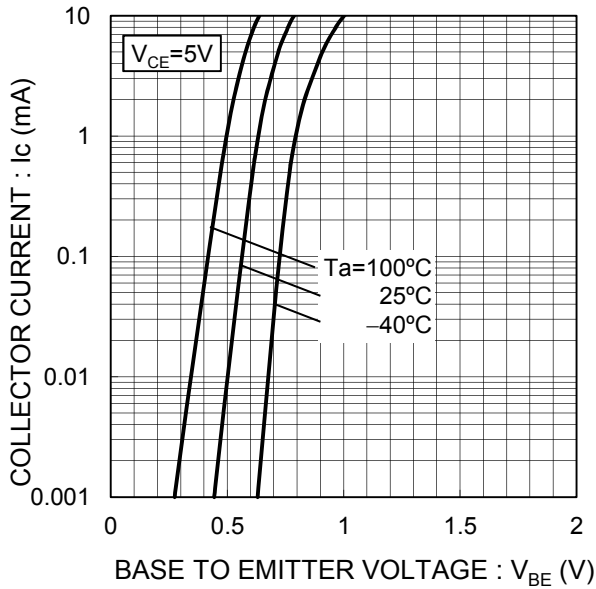


Fig.2 Grounded emitter output characteristics

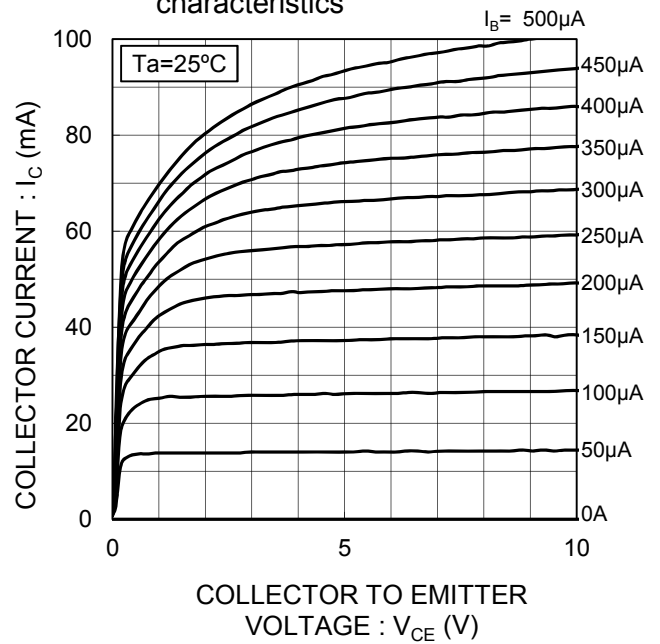


Fig.3 DC Current gain vs. Collector Current

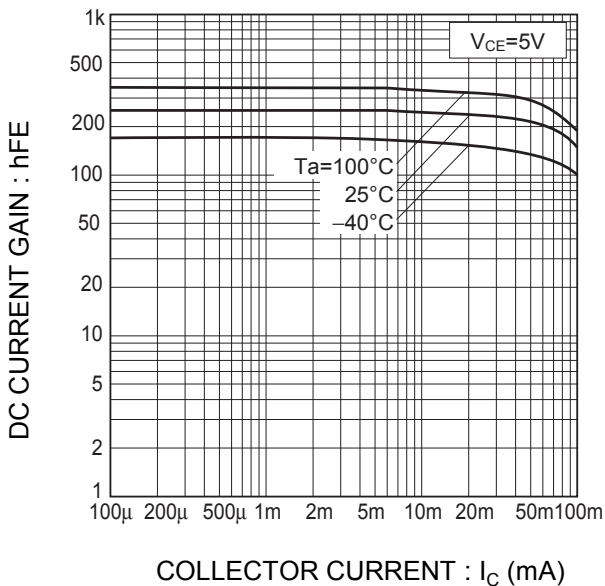
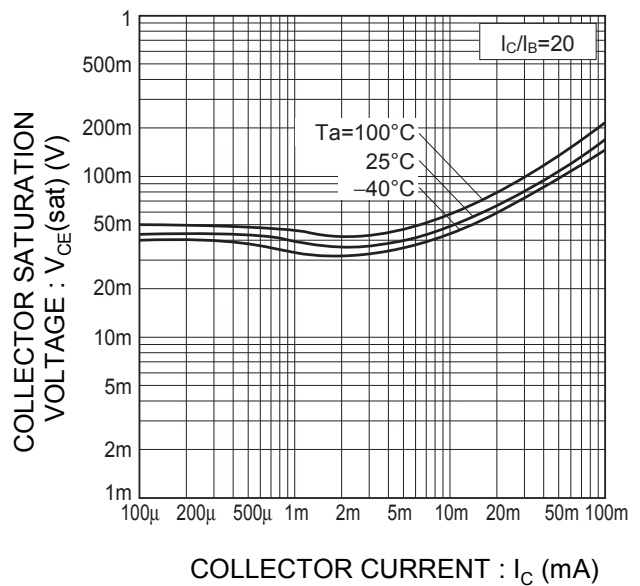
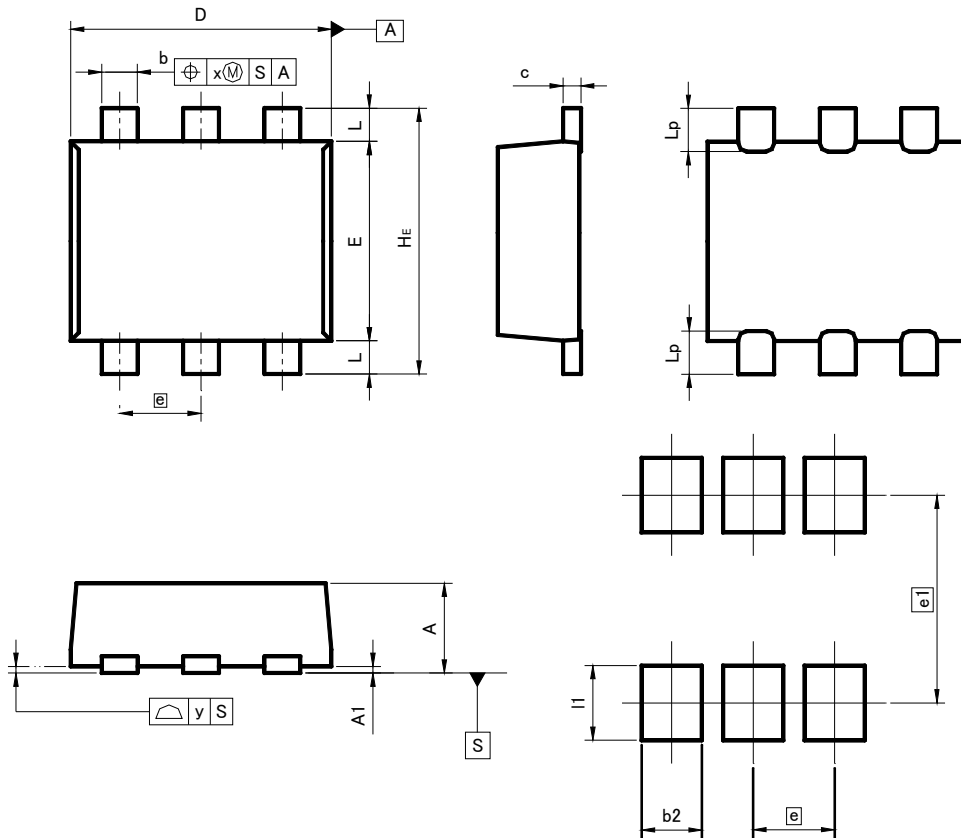


Fig.4 Collector-emitter saturation voltage vs. Collector Current



●Dimensions (Unit : mm)

EMT6



**Pattern of terminal position areas**

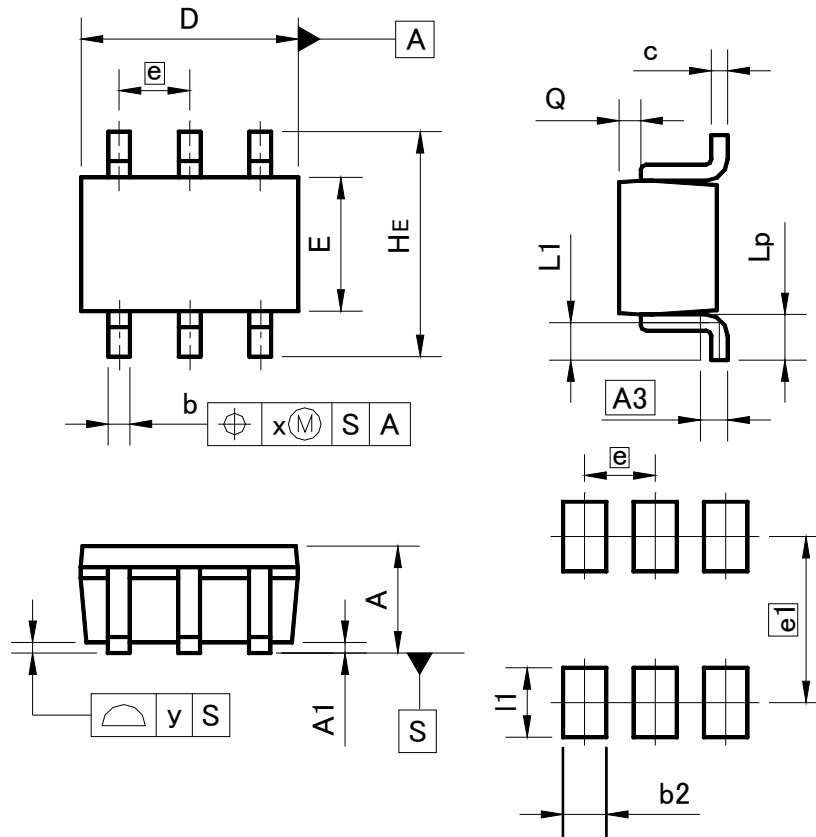
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A1	0.00	0.10	0	0.004
A	0.45	0.55	0.018	0.022
b	0.17	0.27	0.007	0.011
c	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	1.10	1.30	0.043	0.051
e	0.50		0.02	
HE	1.50	1.70	0.059	0.067
L	0.10	0.30	0.004	0.012
Lp	-	0.35	-	0.014
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
e1	1.25		0.049	
b2	-	0.37	-	0.015
l1	-	0.45	-	0.018

Dimension in mm/inches

●Dimensions (Unit : mm)

UMT6



**Pattern of terminal position areas**

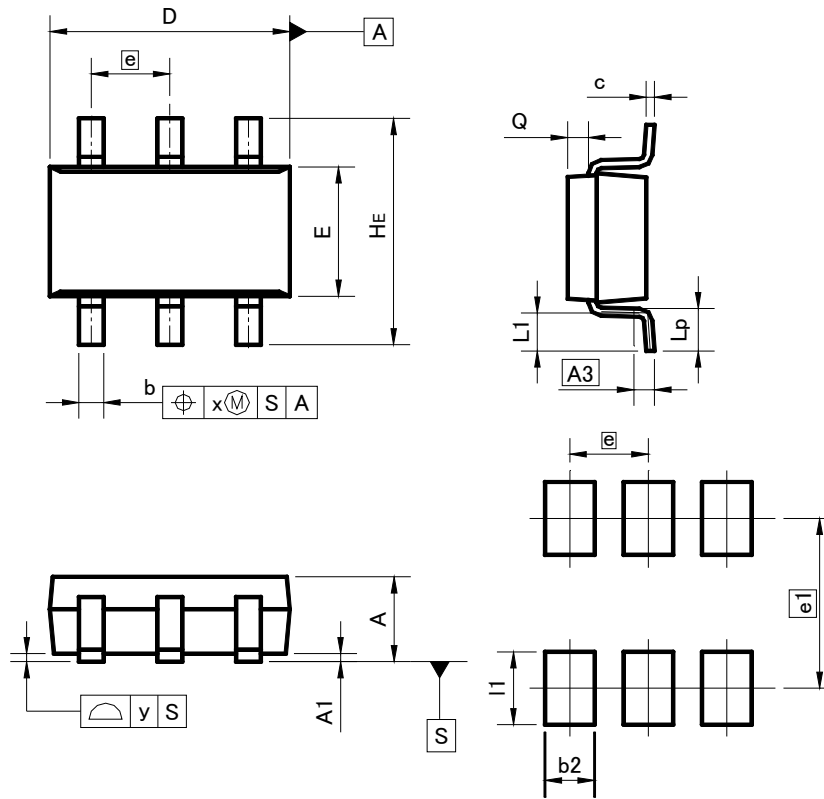
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.80	1.00	-	0.039
A1	0.00	0.10	0	0.004
A3	0.25		0.01	
b	0.15	0.30	0.006	0.012
c	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
e	0.65		0.03	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.02
Lp	0.25	0.55	0.01	0.022
Q	0.10	0.30	0.004	0.012
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
e1	1.55		0.06	
b2	-	0.40	-	0.016
h1	-	0.65	-	0.026

Dimension in mm/inches

●Dimensions (Unit : mm)

SMT6



Pattern of terminal position areas

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.00	1.30	0.039	0.051
A1	0.00	0.10	0	0.004
A3	0.25		0.01	
b	0.25	0.40	0.01	0.016
c	0.09	0.25	0.004	0.01
D	2.80	3.00	0.11	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.04	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
x	-	0.20	-	0.008
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
e1	2.10		0.08	
b2	-	0.60	-	0.024
l1	-	0.90	-	0.035

Dimension in mm/inches

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